

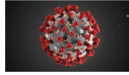
# EE241B : Advanced Digital Circuits

## Lecture 17 – Power-Performance Tradeoffs

### Borivoje Nikolić



March 16, hpcwire.com: Folding@home Turns Its Massive Crowdsourced Computer Network Against COVID-19



### Announcements

- Project midterm reports postponed until Tuesday, March 31
- Assignment 3 postponed until Thursday, April 2.
- Reading – req'd
  - Markovic et al, Methods for true energy-performance optimization, IEEE Journal of Solid-State Circuits, vol. 39, no.8, pp. 1281-1293, August 2004.
  - Chandrakasan and Brodersen, Low power CMOS digital design, IEEE Journal of Solid-State Circuits, vol. 27, no. 4, pp. 473-484, Apr. 1995.
- Recommended
  - Zyuban et al, Integrated Analysis of Power and Performance for Pipelined Microprocessors, IEEE Trans. on Computers, vol.53, no. 8, August 2004.

### Outline

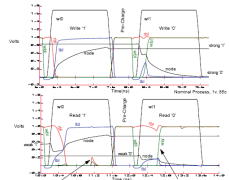
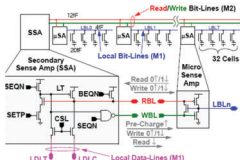
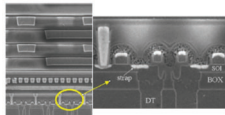
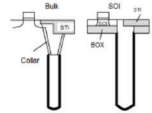
- Module 4
  - SRAM alternatives
- Module 5
  - Low-power design
  - Power-performance tradeoffs



### 4.J SRAM Alternatives

### eDRAM

- Process cost: Added trench capacitor



Barth, ISSCC'07, Wang, IEDM'06

### Crosspoint Memories

- Barrett, IRE Trans. Comp. 1961.

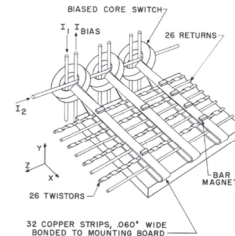
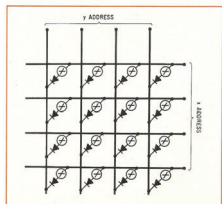


Fig. 2—Memory structure. I1 and I2 are access drive currents to core-selection switch. Presence or absence of a magnet over a twistor-strip solenoid crosspoint yields a "zero" or "one." Signals observed between twistor and return wire.

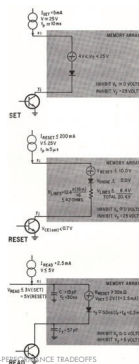
### Crosspoint Memories



- Neale, Nelson, Moore, Electronics '70
  - 16 x 16 array (256b) of 'read-mostly memory'

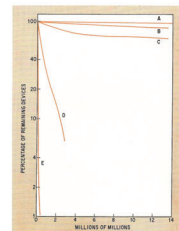


### Crosspoint Memory



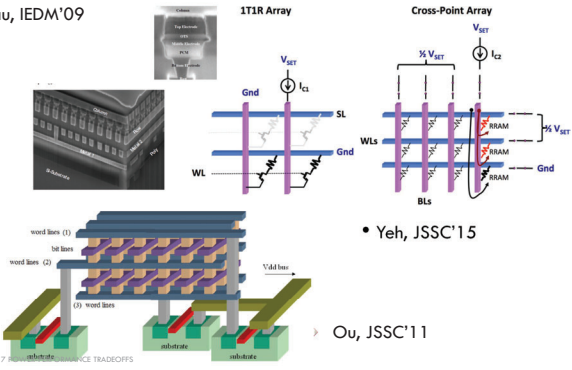
- Four modes
  - Form
  - Set
  - Reset
  - Read

### Endurance



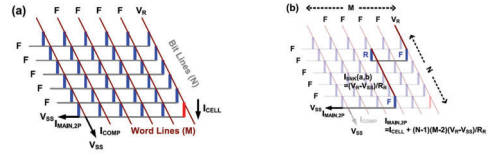
### 3D Crosspoint Arrays

► Kau, IEDM'09



### Crosspoint Arrays

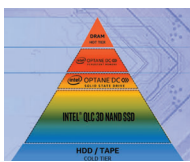
• Read and sneak currents



Boe, TED 4/17

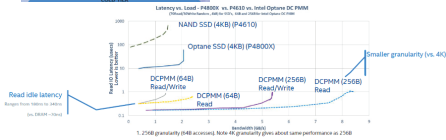
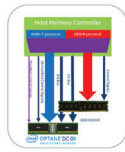
### In the News...

• Intel Optane = 3D XPoint



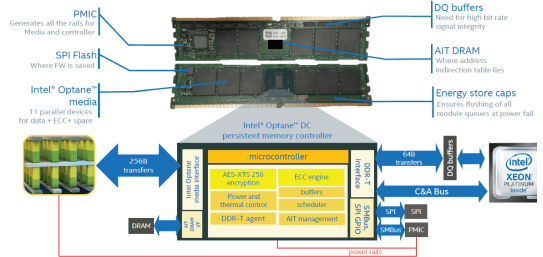
#### DDR-T PROTOCOL

- Protocol on top of electrical/mechanical interface for DDR4
- Allows for asynchronous command/data timing
- Controller uses microprogram scheme to communicate with host controller
- Data bus direction and timing controlled by host
- Customized protocol for persistent memory controller
- Transaction can be re-ordered in the Intel Optane DC persistent memory controller
- 64B cache line access granularity (similar to DDR4)



Performance results are based on testing of Intel® Optane™ DC persistent memory controller and provided for informational purposes. Software and hardware used to generate these results have been optimized for performance only and are not representative of real-world usage. Intel reserves the right to change specifications without notice. For more information, go to [www.intel.com/pressroom](http://www.intel.com/pressroom).

### Optane DDR



### Importance of Power Awareness

- Energy: Crucial for Portable Applications
  - Determines battery lifetime
  - Amount of computation that can be performed
  - Performance is what sells products
- Power: Crucial for High-Performance Applications
  - Determines cooling and energy costs
  - Most designs today are power limited
  - Still need maximum performance

### 5. Low-Power Design



### The Old Design Philosophy

- Maximum performance is primary goal
  - Minimum delay at circuit level
- Architecture implements the required function with target throughput, latency
- At circuit level, supplies, thresholds set to achieve maximum performance, subject to reliability constraints
- Performance achieved through optimum sizing, logic mapping, architectural transformations

### Constant Field Scaling Model

Traditional scaling model

$$\text{If } V_{DD} = 0.7, \text{ and } \text{Freq} = \left(\frac{1}{0.7}\right),$$

$$\text{Power} = CV_{DD}^2 f = \left(\frac{1}{0.7} \times 1.14^2\right) \times (0.7^2) \times \left(\frac{1}{0.7}\right) = 1.3$$

Maintaining the frequency scaling model of 1990s

$$\text{If } V_{DD} = 0.7, \text{ and } \text{Freq} = 2,$$

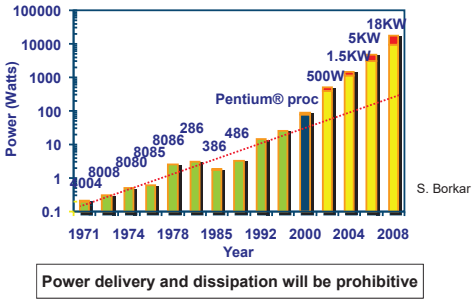
$$\text{Power} = CV_{DD}^2 f = \left(\frac{1}{0.7} \times 1.14^2\right) \times (0.7^2) \times (2) = 1.8$$

While slowing down voltage scaling

$$\text{If } V_{DD} = 0.85, \text{ and } \text{Freq} = 2,$$

$$\text{Power} = CV_{DD}^2 f = \left(\frac{1}{0.7} \times 1.14^2\right) \times (0.85^2) \times (2) = 2.7$$

## 2001 Picture: Power As a Problem



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## The New Design Philosophy

- Maximum performance is too power-hungry, and/or not even practically achievable
- Extract maximum performance under a power/energy envelope
- Excess performance (as offered by technology) to be used for energy/power reduction

17

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Trading off speed for power

18

## 5.A Power and Energy Basics

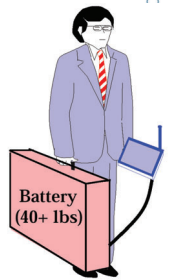


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## Portability: Battery Limits

- Little change in basic technology
  - store energy using a chemical reaction
- Battery capacity doubles every 10 years
  - Has slowed down
- Energy density/size, safe handling are limiting factor

Energy density of material	KWH/kg
Gasoline	14
Lead-Acid	0.04
Li polymer	0.15

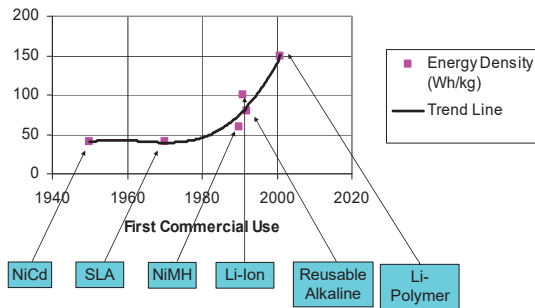


19

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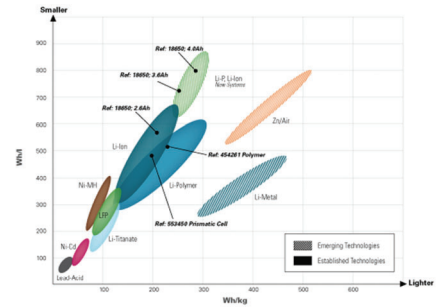
20

## Battery Progress



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## Comparison of Energy Densities for Various Battery Chemistries

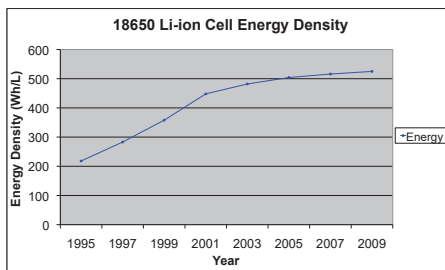


21

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22

## Battery Technology Saturating



Battery capacity naturally plateaus as systems develop

[Courtesy: M. Doyle, Dupont]

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## 5.B Power-Performance Tradeoffs

23

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24

## Know Your Enemy

- Where does power go in CMOS?
- Switching (dynamic) power
  - Charging capacitors
- Leakage power
  - Transistors are imperfect switches
- Short-circuit power
  - Both pull-up and pull-down on during transition
- Static currents
  - Biasing currents

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## Summary of Power Dissipation Sources

$$P \sim \alpha \cdot (C_L + C_{CS}) \cdot V_{swing} \cdot V_{DD} \cdot f + (I_{DC} + I_{Leak}) \cdot V_{DD}$$

- $\alpha$  – switching activity
- $C_L$  – load capacitance
- $C_{CS}$  – short-circuit "capacitance"
- $V_{swing}$  – voltage swing
- $f$  – frequency
- $I_{DC}$  – static current
- $I_{Leak}$  – leakage current

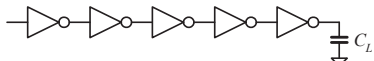
$$P = \frac{\text{energy}}{\text{operation}} \times \text{rate} + \text{static power}$$

25

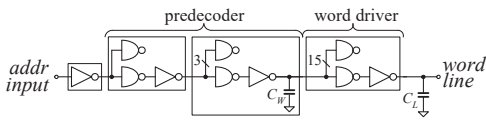
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## CMOS Performance Optimization

- Reminder - sizing: Optimal performance with equal fanout per stage



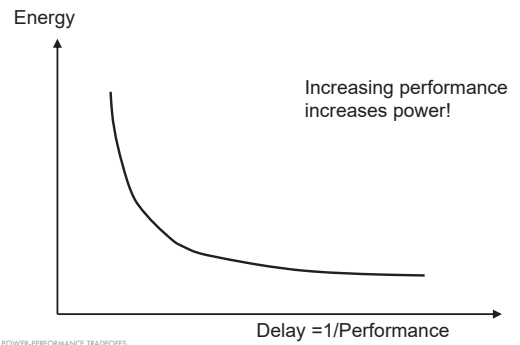
- Extendable to general logic cone through 'logical effort'
- Equal effective fanouts ( $g_i C_{i+1} / C_i$ ) per stage
- Optimal fanout is around 4



[Ref: I. Sutherland, Morgan-Kaufman'98]

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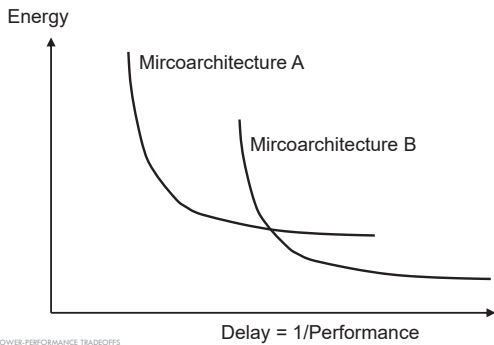
## Performance Optimization



27

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## Performance Optimization



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## Next Lecture

- Spring break
- Low-power design
  - Power-performance tradeoffs

29

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30